RTF025N03

# **Transistors**

# 2.5V Drive Nch MOSFET RTF025N03

#### Structure

Silicon N-channel MOSFET

#### Features

- 1) Low On-resistance.
- 2) Space saving, small surface mount package (TUMT3).
- 3) Low voltage drive (2.5V drive).

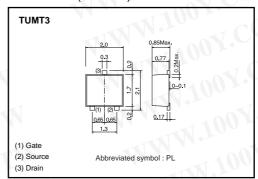
# Applications

Switching

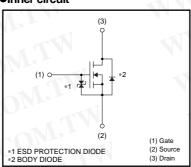
# Packaging specifications

	Package	Taping		
Type	Code	TL		
	Basic ordering unit (pieces)	3000		
RTF025N03	0			

# ● Dimensions (Unit: mm)



#### Inner circuit



# ● Absolute maximum ratings (Ta=25°C)

Parameter Drain-source voltage Gate-source voltage		Symbol	Limits	Unit V V						
		V <sub>DSS</sub>	30							
		V <sub>GSS</sub>	12							
Drain current	Continuous	ID	±2.5	A						
	Pulsed	I <sub>DP</sub> *1	±10	Α						
Source current	Continuous	Is	0.6	A						
(Body diode)	Pulsed	I <sub>SP</sub> *1	10	Α						
Total power dissipation		P <sub>D</sub> *2	0.8	W						
Channel temperature		Tch	150	°C						
Range of storage temperature		Tstg	-55 to +150	.C						

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# Thermal resistance





<sup>\*1</sup> Pw≤10µs, Duty cycle≤1% \*2 Mounted on a ceramic board

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# ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	$\Lambda_{L_{1}}$	_	10	μΑ	Vgs=12V, Vps=0V
Drain-source breakdown voltage	V <sub>(BR) DSS</sub>	30	-		V	I <sub>D</sub> = 1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	I <sub>DSS</sub>		7.	1	μΑ	V <sub>DS</sub> = 30V, V <sub>GS</sub> =0V
Gate threshold voltage	V <sub>GS (th)</sub>	0.5		1.5	V	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA
a	U -	=-	48	67	mΩ	I <sub>D</sub> = 2.5A, V <sub>GS</sub> = 4.5V
Static drain-source on-state resistance	R <sub>DS (on)</sub> *		50	70	mΩ	I <sub>D</sub> = 2.5A, V <sub>GS</sub> = 4V
resistance	$U(I) \mid \mathcal{F} \mid$	_	70	98	mΩ	I <sub>D</sub> = 2.5A, V <sub>GS</sub> = 2.5V
Forward transfer admittance	Y <sub>fs</sub>   *	2	0-12	_	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 2.5A
Input capacitance	Ciss		270	-11	pF	V <sub>DS</sub> = 10V
Output capacitance	Coss	_	70	NJ.	pF	Vgs=0V
Reverse transfer capacitance	Crss	<b>₹</b>	40	_	pF	f=1MHz
Turn-on delay time	td (on) *	) <u>F</u> .	8	1 m	ns	V <sub>DD</sub> ≒ 15V
Rise time	tr *		15	$D\bar{L}_{L}$	ns	ID= 1.25A
Turn-off delay time	t <sub>d (off)</sub> *	-	27	_	ns	V <sub>GS</sub> = 4.5V R <sub>L</sub> =12Ω
Fall time	t <sub>f</sub> *	7	11		ns	$R_{G}=10\Omega$
Total gate charge	Q <sub>g</sub> *	-0	3.7	5.2	nC	V <sub>DD</sub> ≒15V
Gate-source charge	Q <sub>gs</sub> *	THU	0.7	-	nC	V <sub>GS</sub> = 4.5V
Gate-drain charge	Q <sub>gd</sub> *	_	1.2	ŒU.	nC	I <sub>D</sub> = 2.5A
*Pulsed	4	40				144

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# ●Body diode characteristics (Source-drain) (Ta=25°C)

77	Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
ZI CUIVE	Forward voltage	VsD	1.	- ,	1.2	V	I <sub>S</sub> = 0.6A, V <sub>GS</sub> =0V	
07.			- 1	10	nr.			
40								
100								

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**Appendix** 

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